

**Pisni izpit 19. 8. 2019**

Ime in priimek: \_\_\_\_\_

Vpisna številka: \_\_\_\_\_

**Naloga 1**

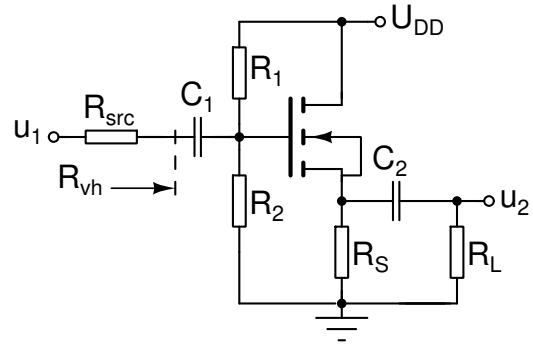
Določite elemente vezja, da bo v delovni točki  $I_D = 0.5\text{mA}$ ,  $U_{DS} = 4\text{V}$ . Vhodna upornost za majhne signale pri srednjih frekvencah naj bo  $R_{vh} = 20\text{k}\Omega$ .

$$U_{DD} = 9\text{V}$$

$$K = 0.2\text{mA/V}^2, U_T = 0.6\text{V}, \lambda = 0$$

$$R_{src} = 50\Omega, R_L = 10\text{k}\Omega$$

$$C_1, C_2 \rightarrow \infty$$

**Naloga 2**

Določite delovno točko tranzistorja ( $I_C, U_{CE}$ ) in izhodno upornost  $R_{izh}$ .

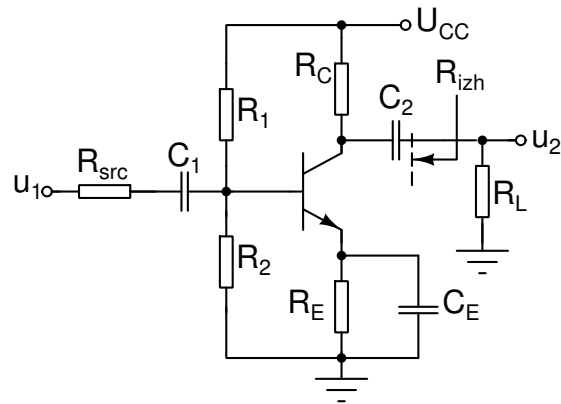
$$U_{CC} = 5\text{V}, R_{src} = 50\Omega, R_L = 10\text{k}\Omega$$

$$\beta = 200, V_{AF} = 100\text{V}$$

$$R_1 = 20\text{k}\Omega, R_2 = 10\text{k}\Omega$$

$$R_C = 1.5\text{k}\Omega, R_E = 500\Omega$$

$$C_1, C_2, C_E \rightarrow \infty$$

**Naloga 3**

Delovni tok tranzistorja je  $I_D = 1.3\text{mA}$ . Določite napetostno ojačenje  $A_u = \frac{U_2}{U_1}$  pri srednjih frekvencah in zgornjo frekvenčno mejo.

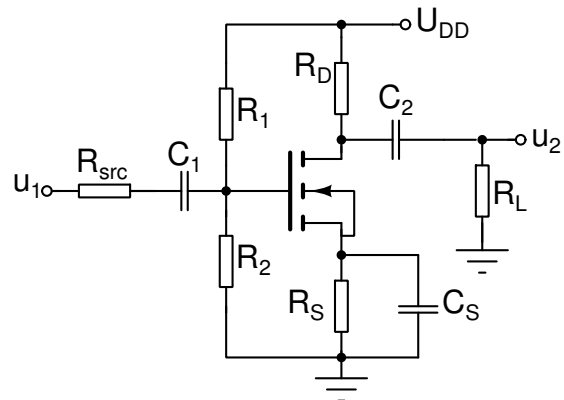
$$U_{DD} = 9\text{V}, R_{src} = 1\text{k}\Omega, R_L = 20\text{k}\Omega$$

$$R_1 = 100\text{k}\Omega, R_2 = 30\text{k}\Omega, R_S = 1\text{k}\Omega, R_D = 5\text{k}\Omega$$

$$C_1 = C_2 = C_S = 10\mu\text{F}$$

$$K = 15\text{mA/V}^2, U_T = 0.4\text{V}, \lambda = 10^{-3}\text{V}$$

$$C_{gs} = 5\text{pF}, C_{gd} = 0.5\text{pF}$$

**Naloga 4**

Določite spodjo frekvenčno mejo za napetostno ojačenje  $A_u = \frac{U_2}{U_1}$ . Admitančni parametri tranzistorja za orientacijo s skupnim emitorjem so:

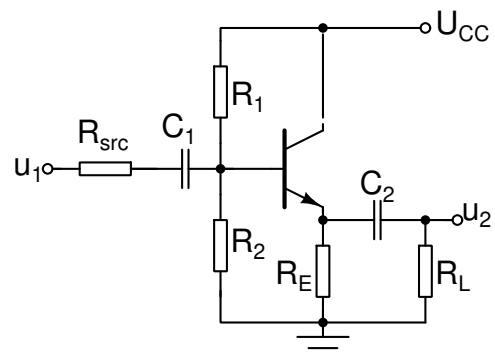
$$Y_E = \begin{bmatrix} 0.19\text{mS} & 0 \\ 44.5\text{mS} & 13.7\mu\text{S} \end{bmatrix}$$

$$U_{CC} = 9\text{V}, R_{src} = 500\Omega, R_L = 1\text{k}\Omega$$

$$\beta = 250, V_{AF} = 80\text{V}$$

$$R_1 = 20\text{k}\Omega, R_2 = 30\text{k}\Omega, R_E = 4\text{k}\Omega$$

$$C_1 \rightarrow \infty, C_2 = 4.7\mu\text{F}$$



Admitančni parametri:

$$\begin{aligned}i_1 &= y_{11}u_1 + y_{12}u_2 \\i_2 &= y_{21}u_1 + y_{22}u_2 \\y_{11} &= \frac{1}{h_{11}}, \quad y_{12} = -\frac{h_{12}}{h_{11}} \\y_{21} &= \frac{h_{21}}{h_{11}}, \quad y_{22} = \frac{D_h}{h_{11}}\end{aligned}$$

$$A_u = -\frac{y_{21}}{y_{22} + Y_L}, \quad A_i = \frac{y_{21}}{y_{11} + Z_L D_y}, \quad Y_{in} = y_{11} - \frac{y_{12}y_{21}}{y_{22} + Y_L}, \quad Y_{out} = y_{22} - \frac{y_{12}y_{21}}{y_{11} + Y_{src}}$$

Hibridni parametri:

$$\begin{aligned}u_1 &= h_{11}i_1 + h_{12}u_2 \\i_2 &= h_{21}i_1 + h_{22}u_2 \\h_{11} &= \frac{1}{y_{11}}, \quad h_{12} = -\frac{y_{12}}{y_{11}} \\h_{21} &= \frac{y_{21}}{y_{11}}, \quad h_{22} = \frac{D_y}{y_{11}}\end{aligned}$$

NMOS (skupni izvor):

za  $u_{GS} > U_T, u_{DS} > u_{GS} - U_T$ :

$$\begin{aligned}i_D &= \frac{1}{2}K(u_{GS} - U_T)^2(1 + \lambda u_{DS}) \\g_{21} &= \frac{2I_D}{U_{GS} - U_T}, \quad g_{22} = \frac{\lambda I_D}{1 + \lambda U_{DS}}\end{aligned}$$

PMOS (skupni izvor):

za  $-u_{GS} > U_T, -u_{DS} > -u_{GS} - U_T$ :

$$\begin{aligned}-i_D &= \frac{1}{2}K(u_{GS} + U_T)^2(1 - \lambda u_{DS}) \\g_{21} &= \frac{2I_D}{U_{GS} + U_T}, \quad g_{22} = \frac{\lambda I_D}{1 - \lambda U_{DS}}\end{aligned}$$

NPN (skupni emitor):

v aktivnem področju:

$$\begin{aligned}g_{11} &= \frac{I_B}{V_T}, \quad g_{21} = \frac{I_C}{V_T}, \\g_{22} &= \frac{I_C}{U_{CE} + V_{AF}} \\ \frac{g_{21}}{g_{11}} &= \beta = \beta_F(1 + \frac{U_{CE}}{V_{AF}})\end{aligned}$$

PNP (skupni emitor):

v aktivnem področju:

$$\begin{aligned}g_{11} &= -\frac{I_B}{V_T}, \quad g_{21} = -\frac{I_C}{V_T}, \\g_{22} &= \frac{-I_C}{-U_{CE} + V_{AF}} \\ \frac{g_{21}}{g_{11}} &= \beta = \beta_F(1 + \frac{-U_{CE}}{V_{AF}})\end{aligned}$$

RC člen - mejna frekvenca:  $f_{-3dB} = \frac{1}{2\pi\tau} = \frac{1}{2\pi R_{eq}C}$ Miller-jev pojav (preslikava impedance med vhom in izhodom tranzistorja z napetostnim ojačenjem  $A_0$  na vhod tranzistorja):

$$Z_{M,vhod} = \frac{Z_{vhod-izhod}}{1-A_0} \Rightarrow \text{za skupni emitor: } C_M = (1 - A_0)C_{bc}$$

Kvadratna enačba:

$$\begin{aligned}ax^2 + bx + c &= 0 \\D &= b^2 - 4ac \\x_{i,2} &= \frac{-b \pm \sqrt{D}}{2a}\end{aligned}$$